

**3V 900MHZ LINEAR POWER
 AMPLIFIER MODULE**

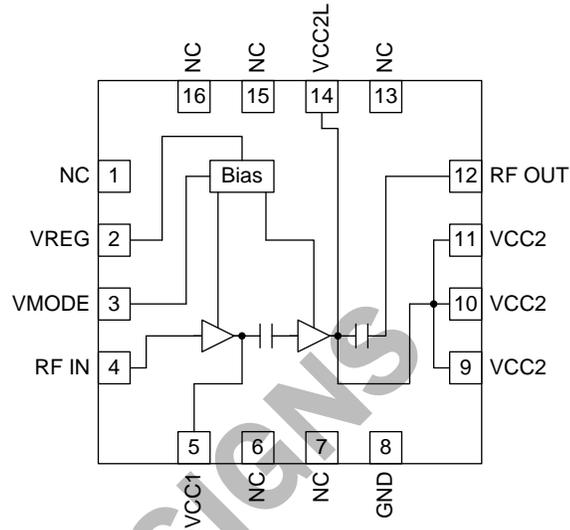
RoHS Compliant & Pb-Free Product
 Package Style: QFN, 16-Pin, 3x3

Features

- Input Internally Matched @ 50Ω
- Output Internally Matched
- 23% Linear Efficiency @ 19dBm
- 40% Linear Efficiency @ 28dBm
- -50dBc ACPR @ 885 kHz
- 18mA Idle Current in LPM

Applications

- 3V CDMA/AMPS Cellular Handset
- 3V CDMA2000/1XRTT Cellular Handset
- 3V CDMA2000/1X-EV-DO US-Cellular Handset
- Spread-Spectrum System



Functional Block Diagram

Product Description

The RF6263 is a high-power, high-efficiency linear amplifier module specifically designed for 3V handheld systems. The device is manufactured on an advanced third generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V IS-95/CDMA2000-1X/AMPS handheld digital cellular equipment, spread-spectrum systems, and other applications in the 824MHz to 849MHz band. The RF6263 has a digital control pin which when enabled will allow the amplifier to operate up to 19dBm output power with reduced current consumption. The low power mode current consumption can be reduced by more than 50% that of a standard power amplifier. The RF6263 is assembled in a 16-pin, 3mmx3mm, QFN package.

Ordering Information

RF6263 3V 900MHz Linear Power Amplifier Module
 RF6263PCBA-41X Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

- | | | | |
|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

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Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---|----------------|------|
| Supply Voltage (RF off) | +8.0 | V |
| Supply Voltage ($P_{OUT} \leq 31$ dBm) | +5.2 | V |
| Control Voltage (V_{REG}) | +3.9 | V |
| Input RF Power | +10 | dBm |
| Mode Voltage (V_{MODE}) | +3.9 | V |
| Operating Temperature | -30 to +110 | °C |
| Storage Temperature | -40 to +150 | °C |
| Moisture Sensitivity Level (IPC/JEDEC J-STD-20) | MSL 2 @ 260 °C | |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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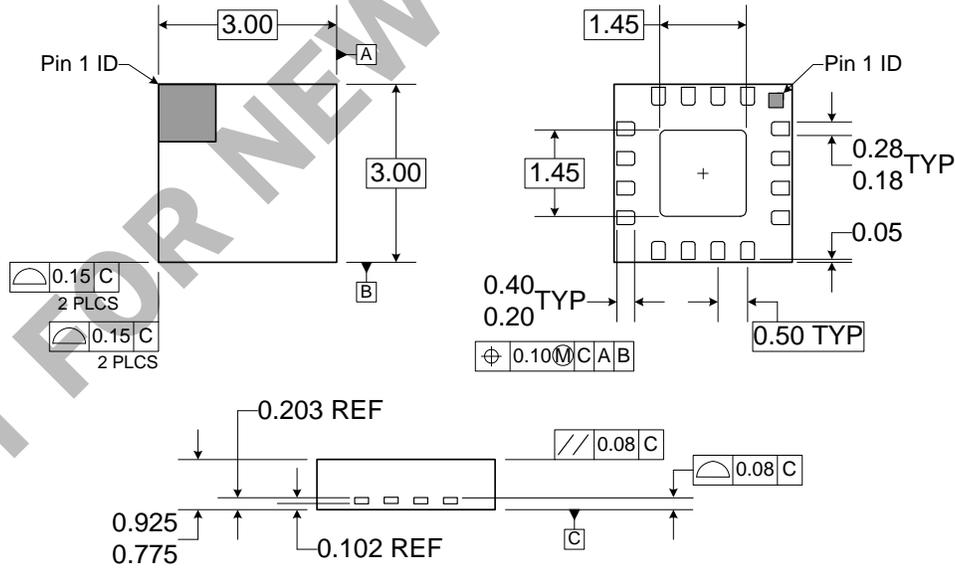
| Parameter | Specification | | | Unit | Condition |
|--|---------------|------|------|--------|---|
| | Min. | Typ. | Max. | | |
| High Power Mode - CDMA (V_{MODE} Low) | | | | | $T = 25^\circ\text{C}$ Ambient, $V_{CC} = 3.4\text{V}$, $V_{REG} = 2.8\text{V}$, $V_{MODE} = 0\text{V}$, and $P_{OUT} = 28\text{dBm}$ for all parameters (unless otherwise specified). |
| Operating Frequency Range | 824 | | 849 | MHz | |
| Linear Gain | | 28 | | dB | |
| Second Harmonics | | -35 | -30 | dBc | |
| Third Harmonics | | -40 | -30 | dBc | |
| Maximum Linear Output | 28 | | | | |
| Linear Efficiency | | 40 | | % | |
| Maximum I_{CC} | | 465 | | mA | |
| ACPR @ 885 kHz | | -50 | | dBc | |
| ACPR @ 1.98 MHz | | -58 | | dBc | |
| Input VSWR | | 2:1 | | | |
| Stability in Band | | | 6:1 | | No oscillation > -70 dBc |
| Stability out of Band | | | 10:1 | | No damage |
| Noise Power | | -133 | | dBm/Hz | At 45 MHz offset. |
| Low Power Mode - CDMA (V_{MODE} High) | | | | | $T = 25^\circ\text{C}$ Ambient, $V_{CC} = 3.4\text{V}$, $V_{REG} = 2.8\text{V}$, $V_{MODE} = 2.8\text{V}$, and $P_{OUT} = 19\text{dBm}$ for all parameters (unless otherwise specified). |
| Operating Frequency Range | 824 | | 849 | MHz | |
| Linear Gain | | 18 | | dB | |
| Maximum Linear Output | 19 | | | | |
| Linear Efficiency | | 23 | | % | |
| Maximum I_{CC} | | 100 | | mA | |
| | | 70 | | mA | $P_{OUT} = 16\text{dBm}$ |
| ACPR @ 885 kHz | | -49 | | dBc | |
| ACPR @ 1.98 MHz | | -62 | | dBc | |
| Input VSWR | | 2:1 | | | |
| Output VSWR Stability | | | 6:1 | | No oscillation > -70 dBc |
| | | | 10:1 | | No damage |

| Parameter | Specification | | | Unit | Condition |
|---|---------------|------|------|------|--|
| | Min. | Typ. | Max. | | |
| FM Mode | | | | | T=25°C Ambient, V _{CC} =3.4V, V _{REG} =2.8V, V _{MODE} =0V, and P _{OUT} =30.5dBm for all parameters (unless otherwise specified). |
| Operating Frequency Range | 824 | | 849 | MHz | |
| AMPS Maximum Output Power | | 30.5 | | dBm | |
| AMPS Efficiency | | 50 | | % | |
| AMPS Gain | | 28 | | | |
| AMPS Second Harmonics | | -35 | -30 | dBc | |
| AMPS Third Harmonics | | -40 | -30 | dBc | |
| Power Supply | | | | | |
| Supply Voltage | 3.2 | 3.4 | 4.2 | V | |
| High Gain Idle Current | | 55 | | mA | V _{MODE} =low and V _{REG} =2.8V |
| Low Gain Idle Current | | 18 | | mA | V _{MODE} =high and V _{REG} =2.8V |
| V _{REG} Current | | 2.5 | | mA | V _{MODE} =high |
| V _{MODE} Current | | 500 | | uA | |
| RF Turn On/Off Time | | | 6 | uS | |
| DC Turn On/Off Time | | | 40 | uS | |
| Total Current (Power Down) | | 0.2 | 2.0 | uA | |
| V _{REG} Low Voltage | 0 | | 0.5 | V | |
| V _{REG} High Voltage (Recommended) | 2.75 | 2.85 | 2.95 | V | |
| V _{REG} High Voltage (Operational) | 2.7 | | 3.0 | V | |
| V _{MODE} Voltage | 0 | | 0.5 | V | High Gain Mode |
| | 2.0 | | 3.0 | V | Low Gain Mode |

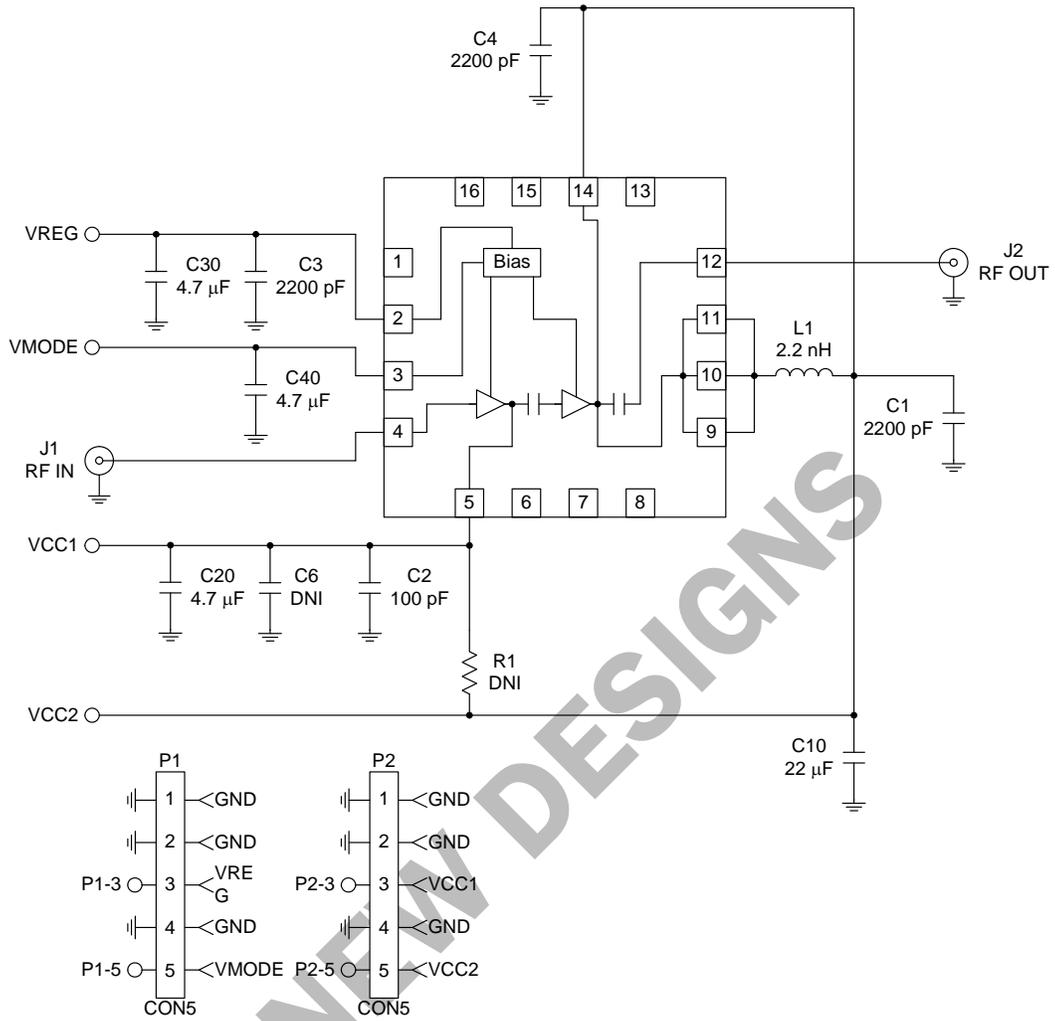
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| Pin | Function | Description | Interface Schematic |
|----------|----------|---|---------------------|
| 1 | NC | No connection. Do not connect this pin to any external circuit. | |
| 2 | VREG | Regulated voltage supply for amplifier bias circuit. In power down mode, both V _{REG} and V _{MODE} need to be LOW (<0.5V). | |
| 3 | VMODE | For nominal operation (High Power mode), V _{MODE} is set LOW. When set HIGH, devices are biased lower to improve efficiency. | |
| 4 | RF IN | RF input internally matched to 50Ω. This input is internally AC-coupled. | |
| 5 | VCC1 | First stage collector supply. A 2200 pF and 4.7 μF decoupling capacitor are required. | |
| 6 | NC | No connection. Do not connect this pin to any external circuit. | |
| 7 | NC | No connection. Do not connect this pin to any external circuit. | |
| 8 | NC | No connection. Do not connect this pin to any external circuit. | |
| 9 | VCC2 | High power output stage collector supply. Refer to schematic for required external components. | |
| 10 | VCC2 | Same as pin 9. | |
| 11 | VCC2 | Same as pin 9. | |
| 12 | RF OUT | RF output. Internally AC-coupled. | |
| 13 | NC | No connection. Do not connect this pin to any external circuit. | |
| 14 | VCC2L | Low power output stage collector supply. Refer to schematic for required external components. | |
| 15 | NC | No connection. Do not connect this pin to any external circuit. | |
| 16 | NC | No connection. Do not connect this pin to any external circuit. | |
| Pkg Base | GND | Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane. | |

Package Drawing



Evaluation Board Schematic - CDMA



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PCB Design Requirements

PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

PCB Land Pattern Recommendation

PCB land patterns for PFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

PCB Metal Land Pattern

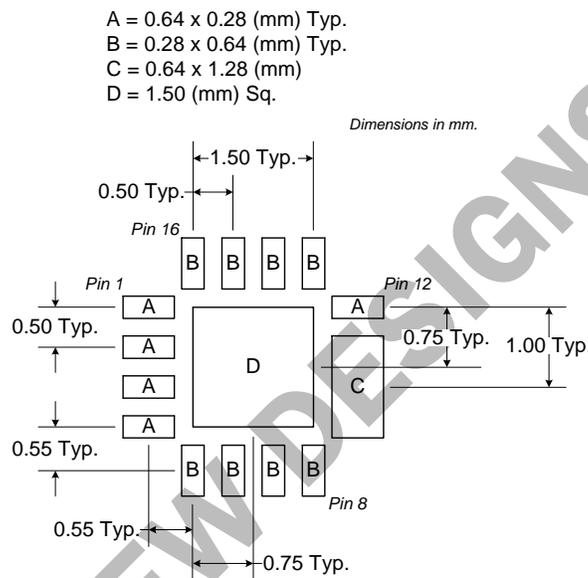


Figure 1. PCB Metal Land Pattern (Top View)

PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

A = 0.74 x 0.38 (mm) Typ.
B = 0.38 x 0.74 (mm) Typ.
C = 1.60 (mm) Sq.

Dimensions in mm.

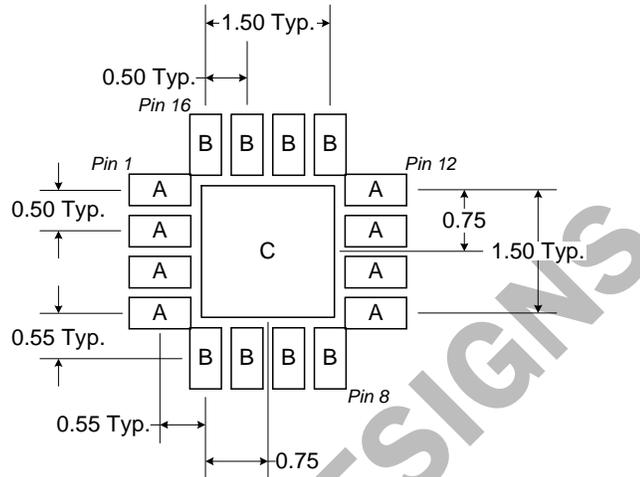


Figure 2. PCB Solder Mask Pattern (Top View)

Thermal Pad and Via Design

The PCB land pattern has been designed with a thermal pad that matches the die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

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Tape and Reel Information

Carrier tape basic dimensions are based on EIA481. The pocket is designed to hold the part for shipping and loading onto SMT manufacturing equipment, while protecting the body and the solder terminals from damaging stresses. The individual pocket design can vary from vendor to vendor, but width and pitch will be consistent.

Carrier tape is wound or placed onto a shipping reel either 330 mm (13 inches) in diameter or 178 mm (7 inches) in diameter. The center hub design is large enough to ensure the radius formed by the carrier tape around it does not put unnecessary stress on the parts.

Prior to shipping, moisture sensitive parts (MSL level 2a-5a) are baked and placed into the pockets of the carrier tape. A cover tape is sealed over the top of the entire length of the carrier tape. The reel is sealed in a moisture barrier, ESD bag, which is placed in a cardboard shipping box. It is important to note that unused moisture sensitive parts need to be resealed in the moisture barrier bag. If the reels exceed the exposure limit and need to be rebaked, most carrier tape and shipping reels are not rated as bakeable at 125 °C. If baking is required, devices may be baked according to section 4, table 4-1, column 8 of Joint Industry Standard IPC/JEDEC J-STD-033A.

The following table provides useful information for carrier tape and reels used for shipping the devices described in this document.

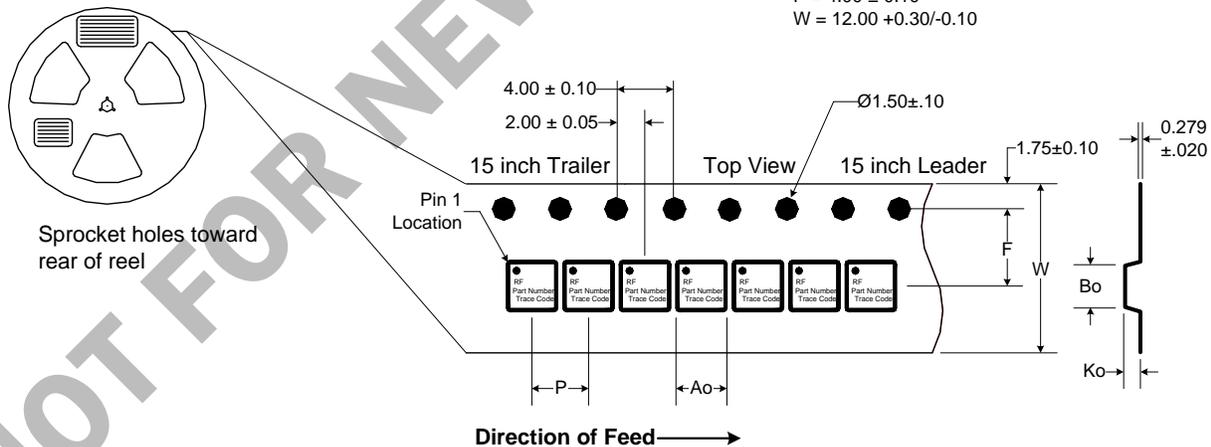
| RFMD Part Number | Reel Diameter Inch (mm) | Hub Diameter Inch (mm) | Width (mm) | Pocket Pitch (mm) | Feed | Units per Reel |
|------------------|-------------------------|------------------------|------------|-------------------|--------|----------------|
| RF6263TR7 | 7 (178) | 2.4 (61) | 12 | 4 | Single | 2500 |

QFN (Carrier Tape Drawing with Part Orientation)

Notes:

1. All dimensions are in millimeters (mm).
2. Unless otherwise specified, all dimension tolerances per EIA-481.

$A_o = 3.18 \pm 0.10$
 $B_o = 3.18 \pm 0.10$
 $F = 5.50 \pm 0.05$
 $K_o = 1.02 \pm 0.10$
 $P = 4.00 \pm 0.10$
 $W = 12.00 +0.30/-0.10$



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